Average gate power dissipation (T_j=125)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	20	W
Peak pulse voltage (T_j=25 ; nonrepetitive,off-state;FIG.7)	V_{pp}	0.5	kV

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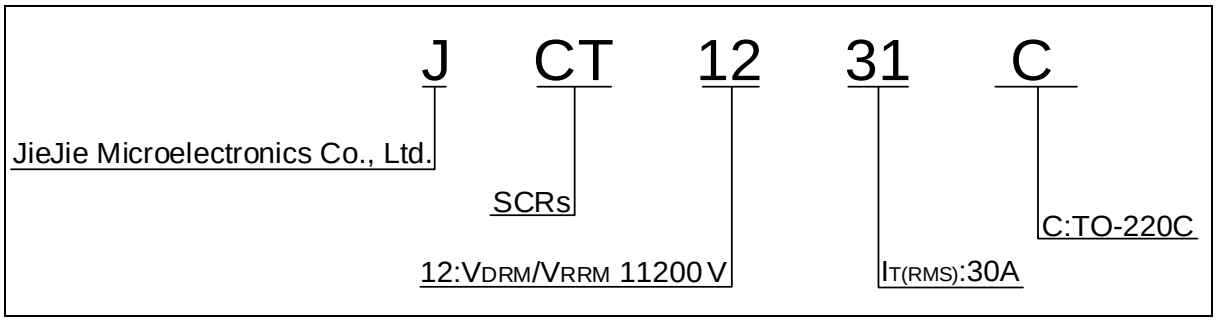


FIG.1: Maximum power dissipation versus RMS on-state current

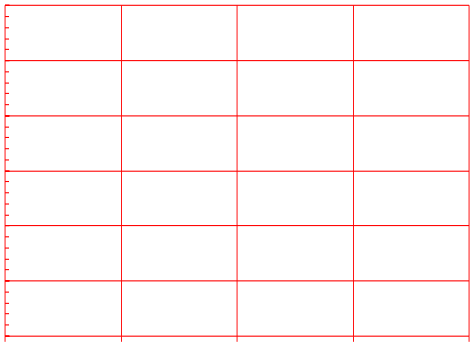
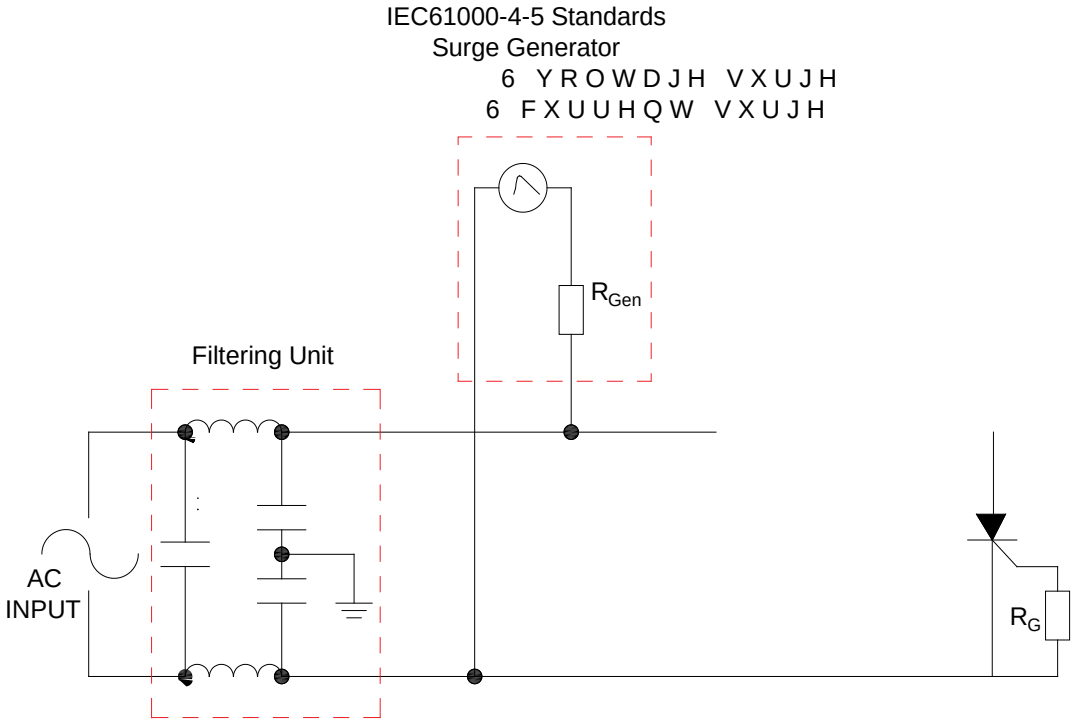


FIG.2: RMS on-state current versus case temperature

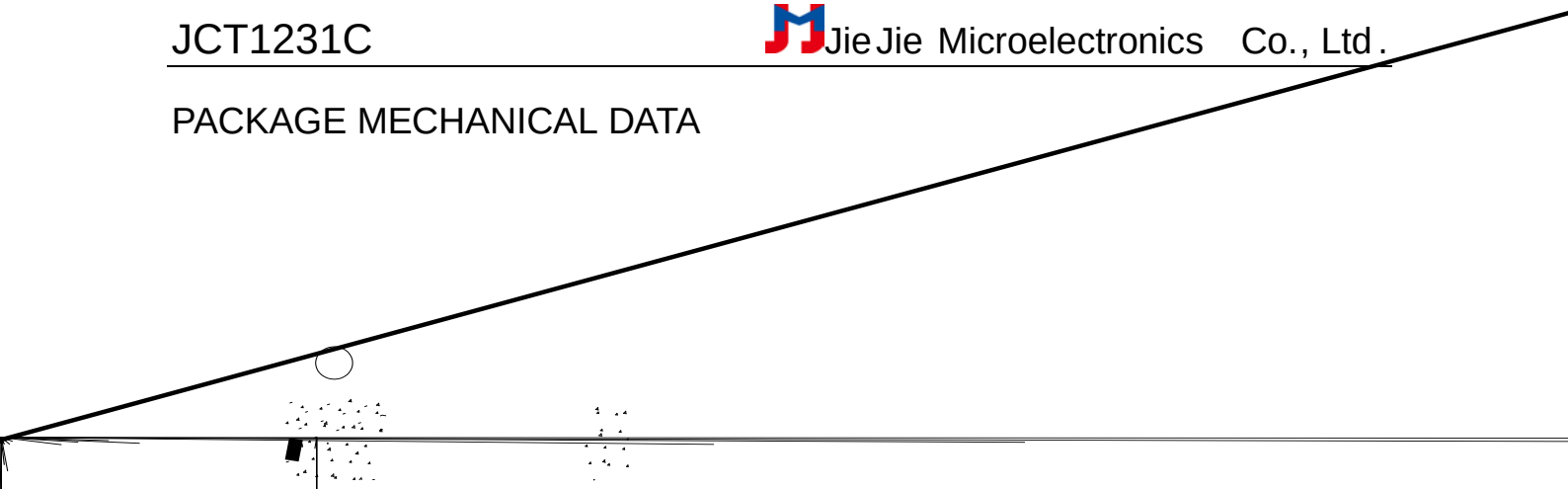
FIG.7 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards.



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